## IN THE CLAIMS:

Listing of claims:

1. (currently amended) A method for forming a head suspension assembly, comprising:

forming a trench extending into a substrate;

forming a first layer comprising a sacrificial layer in the trench;

forming a film across a second layer comprising a resin across the trench the substrate;

forming a third layer comprising a photoresist layer on the second layer and patterning a the photoresist layer on top of the second layer; film;

transferring the <u>an</u> image of the patterned <u>photoresist</u> layer through the <u>second layer</u>; film; removing the patterned photoresist layer; <del>and</del>

removing the sacrificial layer to form a cavity extending a distance into the substrate; and positioning a slider on the second layer after the removing the sacrificial layer.

- 2. (currently amended) A method as in claim 1, wherein the <u>second layer film</u> includes silicon.
- 3. (currently amended) A method as in claim 1, wherein the transferring the image of the patterned photoresist layer through the second layer film is done using reactive ion etching.
- 4. (original) A method as in claim 1, wherein the substrate comprises silicon and the sacrificial layer is formed by etching a trench in the substrate and filling the trench with a metal.
- 5. (currently amended) A method as in claim 4, wherein removing the sacrificial layer comprises etching the metal from the trench after the removing the patterned photoresist layer.
  - 6. (canceled)

- 7. (currently amended) A method as in claim 1, wherein the substrate comprises silicon and the <u>resin</u> film comprises polysilsesquioxone.
- 8. (previously presented) A method as in claim 1, wherein the cavity extends a width that is no greater than that of the substrate and the cavity extends a depth that is less than a depth of the substrate.
- 9. (currently amended) A method as in claim 1, further comprising forming <u>a</u> fourth layer comprising an adhesion layer between the substrate and the <u>second layer</u>. film.
- 10. (currently amended) A method as in claim 3, 1, wherein, prior to the patterning the photoresist layer, the film is at least one of cured, cross-linked, and oxidized. comprises a resin, and positioning a slider on the resin after the removing the sacrificial layer.

## 11-20 (canceled)

21. (new) A method for forming a head suspension assembly, comprising: forming a sacrificial layer in or on a portion of a substrate;

forming a polysilsesquioxone layer on the substrate and on at least part of the sacrificial layer;

forming a photoresist layer on the polysilsesquioxone layer;

patterning the photoresist layer;

etching the polysilsesquioxone layer using the patterned photoresist layer as a mask; removing the patterned photoresist layer to expose remaining polysilsesquioxone layer; removing the sacrificial layer to form a cavity extending a distance into the substrate; and positioning a slider on the remaining polysilsesquioxone layer.

22. (new) The method of claim 21, further comprising curing the polysilsesquioxone layer.

- 23. (new) The method of claim 22, wherein the curing is carried out prior to the positioning a slider on the remaining polysilsesquioxone layer.
- 24. (new) The method of claim 22, wherein the curing is controlled so that cross-linking of the polysilsesquioxone layer occurs.
- 25. (new) The method of claim 21, further comprising cross-linking the polysilsesquioxone layer.
- 26. (new) The method of claim 21, further comprising oxidizing the polysilsesquioxone layer.
- 27. (new) The method of claim 21, further comprising positioning the slider to be on a part of the remaining polysilsesquioxone layer that is positioned over the cavity.
  - 28. (new) A method for forming a head suspension assembly, comprising: forming a sacrificial layer extending a distance into a substrate; forming a resin layer on the substrate and on at least part of the sacrificial layer; forming a photoresist layer on the resin layer; patterning the photoresist layer; etching the resin layer using the patterned photoresist layer as a mask; removing the patterned photoresist layer to expose remaining resin layer;

layer and the substrate; and

removing the sacrificial layer to form a cavity between at least part of the remaining resin

positioning a slider on the remaining resin layer.

29. (new) The method of claim 28, further comprising heating the resin layer prior to the forming a photoresist layer on the resin layer.

- 30. (new) The method of claim 28, wherein resin layer comprises polysilsesquioxone.
- 31. (new) The method of claim 28, further comprising cross-linking at least part of the resin layer prior to the forming the photoresist layer on the resin layer.